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Correction: Aliovalent A-site engineered AgNbO₃ lead-free antiferroelectric ceramics toward superior energy storage density

Nengneng Luo,^{*af} Kai Han,^a Fangping Zhuo,^b Chao Xu,^c Guangzu Zhang,^d Lajun Liu,^e Xiyong Chen,^a Changzheng Hu,^e Huanfu Zhou^e and Yuezhou Wei^{*a}

Correction for 'Aliovalent A-site engineered AgNbO₃ lead-free antiferroelectric ceramics toward superior energy storage density' by Nengneng Luo *et al.*, *J. Mater. Chem. A*, 2019, DOI: 10.1039/c9ta02053e.

The authors regret an error in the published article. The phrase “In contrast, the $\Delta G_{\text{FE-AFE}}$ for the FE-to-AFE phase transition is flattened, corresponding to decreased E_A ” should instead have read as follows: “The $\Delta G_{\text{FE-AFE}}$ for the FE-to-AFE phase transition, in contrast, is flattened, which also contributes to increased E_A ”.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^aGuangxi Key Laboratory of Processing for Non-ferrous Metallic and Featured Materials, School of Resources, Environment and Materials, Guangxi University, Nanning 530004, China. E-mail: luonn1234@163.com; yzwei@gxu.edu.cn

^bDepartment of Chemistry, Tsinghua University, Beijing 100084, China

^cDepartment of Applied Physics, The Hong Kong Polytechnic University, Kowloon, Hong Kong SAR

^dSchool of Optical and Electronic Information, Huazhong University of Science and Technology, Wuhan 430074, China

^eCollege of Materials Science and Engineering, Guilin University of Technology, Guilin 541004, China

^fCenter on Nanoenergy Research, School of Physical Science and Technology, Guangxi University, Nanning 530004, China

